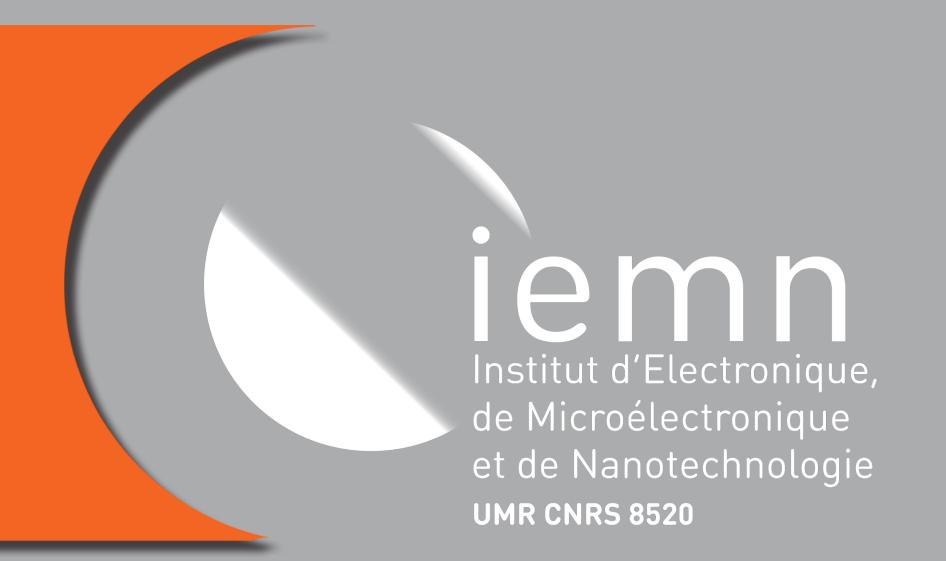
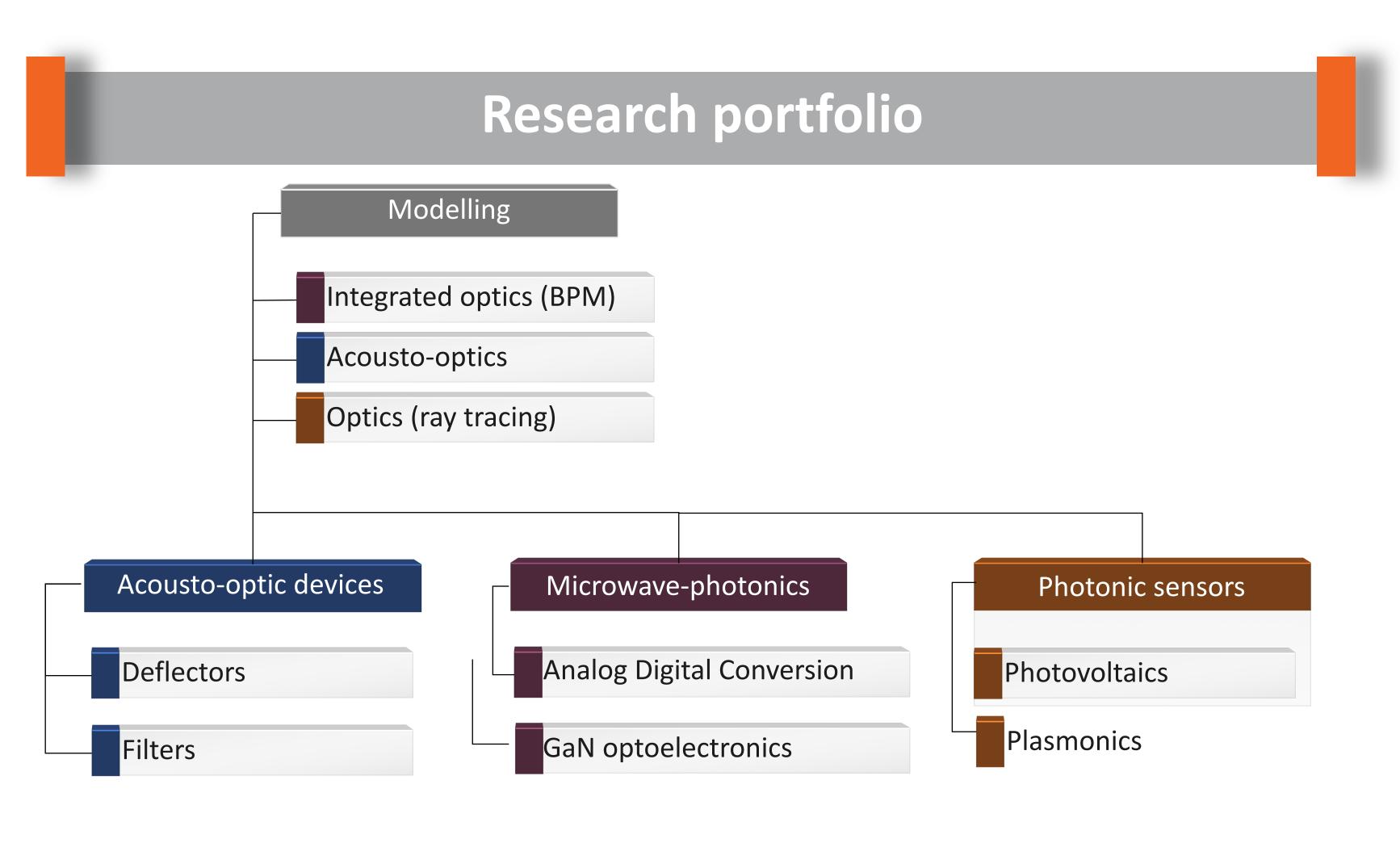
OPTOelectronic Group



Members: E. Dogheche (Pr.), S. Dupont (Pr.), J. Gazalet (Pr.), M. Halbwax (Ass. Pr.), J. Harari (Ass. Pr. HDR), J-C. Kastelik (Pr.), V. Magnin (Ass. Pr.), S. Maricot (Ass. Pr.), C. Sion (Ass. Pr.), J-P. Vilcot (DR).

acousto-optics domains.

developments.



Modelling activities Light propagation in integrated Light trapping structures (ray-tracing) optics/optoelectronics (3D-BPM) Solar cell reflectivity depending on surface texturisation (pyramids) Waveguide design for linear evanescent coupling between Si₃N₄/SiO₂ waveguide and GaAs detector Inverted (linear profile) pa(1), pa(2) Si₃N₄ EHT = 5,00 kV Signal A = InLens Signal = 1,000 WD = 5.9 mm Mag = 5,90 KX Signal B = InLens Mexing = Off Stage at T = 0.0 lemm 200 nm (a.u.) O₂/SF₆ cryogenic plasma etching LT-GaAs Propagation length (µm) Collaboration with iemn THz-Photonics

The group has an historical research activity in the microwaves photonics and

The modelling activity supports the device research and is adapted to its

Photonic sensor thematics started in the early 2010s.

